



SOT-23 Plastic-Encapsulate Diodes

CMPSH-3/3A/3C/3S SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 350 mW ($T_{amb}=25^{\circ}C$)

Forward Current

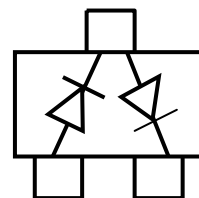
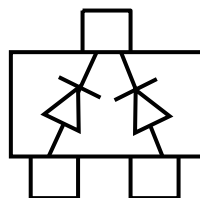
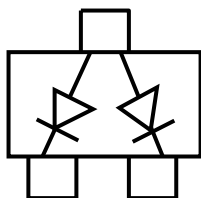
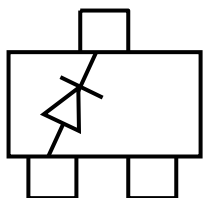
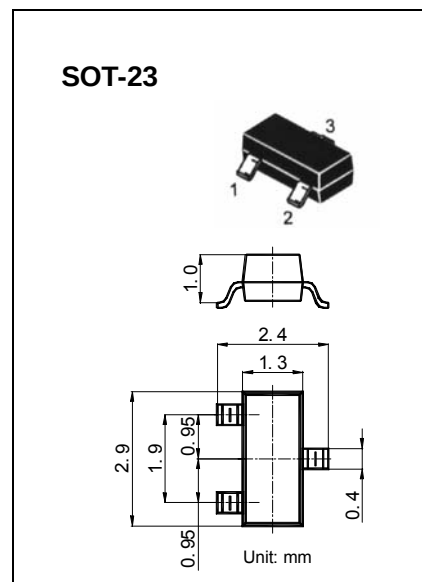
I_F : 100 mA

Reverse Voltage

V_R : 30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+15^{\circ}C$



CMPSH-3 Marking: D95

CMPSH-3A Marking: DB1

CMPSH-3C Marking: DB2

CMPSH-3S Marking: DA5

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	30		V
Reverse voltage leakage current	I_R	$V_R=25V$		500	nA
		$V_R=25V, T_A=100^{\circ}C$		100	μA
Forward voltage	V_F	$I_F=2mA$		0.33	V
		$I_F=15mA$		0.45	
		$I_F=100mA$		1	
Diode capacitance	C_{tot}	$V_R=0V, f=1MHz$		8	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{RR}=1.0mA, R_L=100\Omega$		5	ns